

ZTX795ASTZ Datasheet

www.digi-electronics.com



<https://www.DiGi-Electronics.com>

DiGi Electronics Part Number	ZTX795ASTZ-DG
Manufacturer	Diodes Incorporated
Manufacturer Product Number	ZTX795ASTZ
Description	TRANS PNP 140V 0.5A E-LINE
Detailed Description	Bipolar (BJT) Transistor PNP 140 V 500 mA 100MHz 1 W Through Hole E-Line (TO-92 compatible)



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.

Purchase and inquiry

Manufacturer Product Number:

ZTX795ASTZ

Series:

-

Transistor Type:

PNP

Voltage - Collector Emitter Breakdown (Max):

140 V

Current - Collector Cutoff (Max):

100nA (ICBO)

Power - Max:

1 W

Operating Temperature:

-55°C ~ 200°C (TJ)

Package / Case:

E-Line-3, Formed Leads

Base Product Number:

ZTX795

Manufacturer:

Diodes Incorporated

Product Status:

Active

Current - Collector (Ic) (Max):

500 mA

Vce Saturation (Max) @ Ib, Ic:

250mV @ 50mA, 500mA

DC Current Gain (hFE) (Min) @ Ic, Vce:

300 @ 10mA, 2V

Frequency - Transition:

100MHz

Mounting Type:

Through Hole

Supplier Device Package:

E-Line (TO-92 compatible)

Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.29.0075

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99

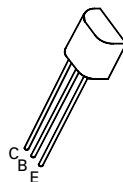
PNP SILICON PLANAR MEDIUM POWER HIGH GAIN TRANSISTOR

ZTX795A

ISSUE 1 – APRIL 94

FEATURES

- * 140 Volt V_{CE0}
- * Gain of 250 at $I_C=0.2$ Amps
- * Very low saturation voltage



E-Line
T092 Compatible

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-140	V
Collector-Emitter Voltage	V_{CEO}	-140	V
Emitter-Base Voltage	V_{EBO}	-5	V
Peak Pulse Current	I_{CM}	-1	A
Continuous Collector Current	I_C	-0.5	A
Practical Power Dissipation*	P_{totp}	1.5	W
Power Dissipation at $T_{amb}=25^\circ\text{C}$ derate above 25°C	P_{tot}	1 5.7	W mW/ $^\circ\text{C}$
Operating and Storage Temperature Range	$T_{j}; T_{stg}$	-55 to +200	$^\circ\text{C}$

*The power which can be dissipated assuming the device is mounted in a typical manner on a P.C.B. with copper equal to 1 inch square minimum

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-140			V	$I_C=-100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-140			V	$I_C=-10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			V	$I_E=-100\mu\text{A}$
Collector Cut-Off Current	I_{CBO}			-0.1	μA	$V_{CB}=-100\text{V}$
Emitter Cut-Off Current	I_{EBO}			-0.1	μA	$V_{EB}=-4\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.3 -0.3 -0.25	V V V	$I_C=100\text{mA}, I_B=1\text{mA}^*$ $I_C=200\text{mA}, I_B=5\text{mA}^*$ $I_C=500\text{mA}, I_B=50\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			-0.95	V	$I_C=500\text{mA}, I_B=50\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-0.75		V	$I_C=500\text{mA}, V_{CE}=-2\text{V}^*$
Static Forward Current Transfer Ratio	h_{FE}	300 250 100		800		$I_C=10\text{mA}, V_{CE}=-2\text{V}^*$ $I_C=200\text{mA}, V_{CE}=-2\text{V}^*$ $I_C=300\text{mA}, V_{CE}=-2\text{V}^*$

ZTX795A

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$)

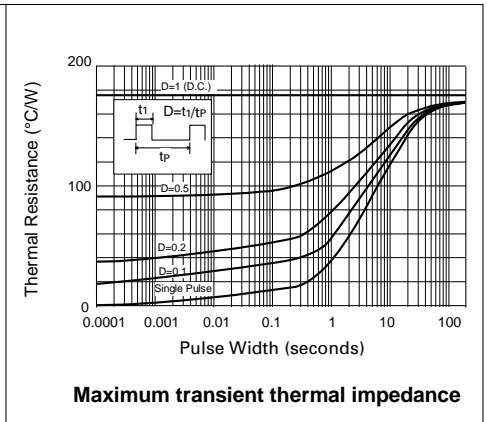
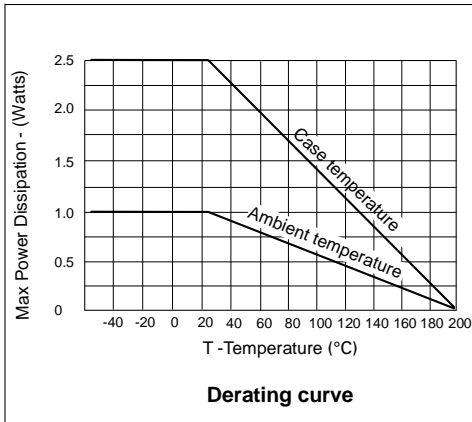
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Transition Frequency	f_T	100			MHz	$I_C = 50\text{mA}$, $V_{CE} = 5\text{V}$ $f = 50\text{MHz}$
Input Capacitance	C_{ibo}		225		pF	$V_{EB} = 0.5\text{V}$, $f = 1\text{MHz}$
Output Capacitance	C_{obo}		15		pF	$V_{CB} = 10\text{V}$, $f = 1\text{MHz}$
Switching Times	t_{on} t_{off}		100 1900		ns ns	$I_C = 100\text{mA}$, $I_{B1} = 10\text{mA}$ $I_{B2} = 10\text{mA}$, $V_{CC} = 50\text{V}$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$

THERMAL CHARACTERISTICS

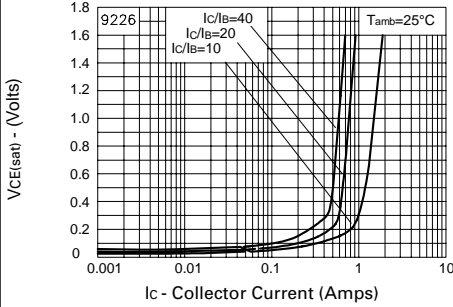
PARAMETER	SYMBOL	MAX.	UNIT
Thermal Resistance Junction to Ambient ₁	$R_{th(j-amb)1}$	175	$^{\circ}\text{C/W}$
Junction to Ambient ₂	$R_{th(j-amb)2} \dagger$	116	$^{\circ}\text{C/W}$
Junction to Case	$R_{th(j-case)}$	70	$^{\circ}\text{C/W}$

† Device mounted on P.C.B. with copper equal to 1 sq. Inch minimum.

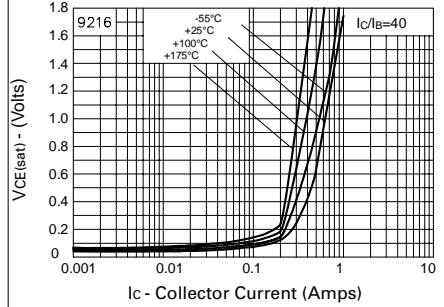


ZTX795A

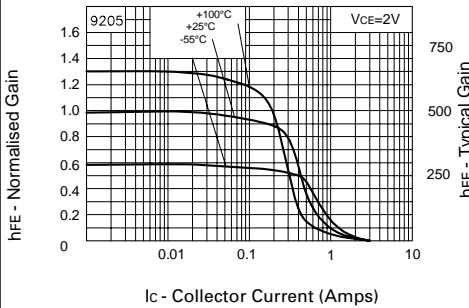
TYPICAL CHARACTERISTICS



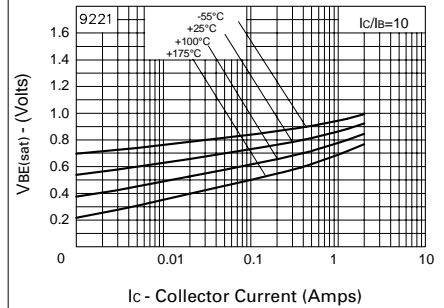
VCE(sat) v IC



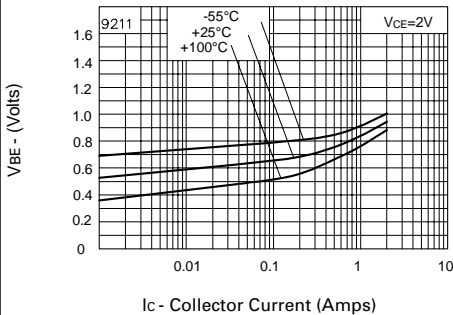
VCE(sat) v IC



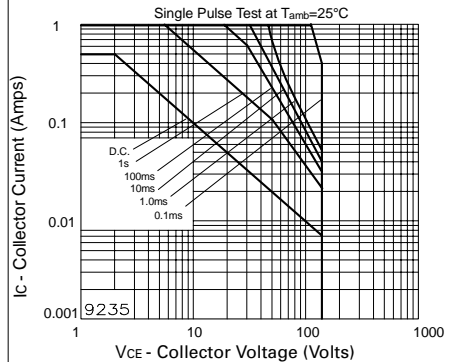
hFE v IC



VBE(sat) v IC



VBE(on) v IC



Safe Operating Area

OUR CERTIFICATE

DiGi provide top-quality products and perfect service for customer worldwide through standardization, technological innovation and continuous improvement. DiGi through third-party certification, we stricly control the quality of products and services. Welcome your RFQ to

Email: Info@DiGi-Electronics.com



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.